TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MH367FK,TC7MH368FK

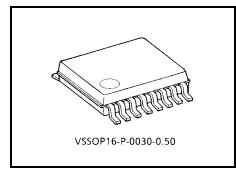
HEX Bus Buffer

TC7MH367FK Non-Inverted, 3-State Outputs TC7MH368FK Inverted, 3-State Outputs

The TC7MH367FK and TC7MH368FK are advanced high speed CMOS HEX bus buffers fabricated with silicon gate $\rm C^2MOS$ technology.

They achieve the high speed operation similar to equivalent bipolar schottky TTL while maintaining the CMOS low power dissipation.

They contain six buffers; four buffers are controlled by an enable input $(\overline{G}1)$, and the other two buffers are controlled by another enable input $(\overline{G}2)$. The outputs of each buffer group are enabled when $\overline{G}1$ and/or $\overline{G}2$ inputs are held low; if held high, these outputs are in a high impedance state.



Weight: 0.02 g (typ.)

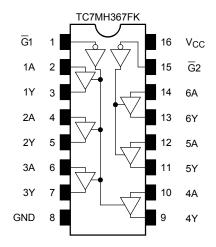
The TC7MH367FK is a non-inverting output type, while the TC7MH368FK is an inverting output type.

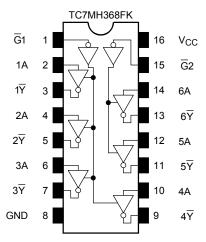
An input protection circuit ensures that 0 to 5.5 V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5 V to 3 V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

Features

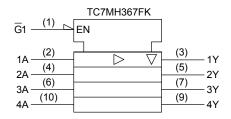
- High speed: $t_{pd} = 3.8 \text{ ns (typ.)} (V_{CC} = 5 \text{ V})$
- Low power dissipation: $I_{CC} = 4 \mu A \text{ (max) (Ta} = 25 ^{\circ}\text{C)}$
- High noise immunity: V_{NIH} = V_{NIL} = 28% V_{CC} (min)
- Power down protection is provided on all inputs.
- Balanced propagation delays: $t_{pLH} \approx t_{pHL}$
- Wide operating voltage range: $V_{CC (opr)} = 2 \sim 5.5 \text{ V}$
- Low noise: VOLP = 0.8 V (max)
- Pin and function compatible with 74ALS367/368

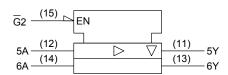
Pin Assignment (top view)

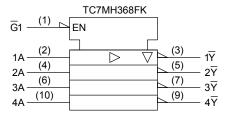


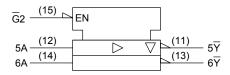


IEC Logic Symbol









Truth Table

Inp	uts	Outputs				
G	Α	Y (367)	Y (368)			
L	L	L	Н			
L	Н	Н	L			
Н	Х	Z	Z			

- X: Don't care
- Z: High impedance



Absolute Maximum Ratings (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	-0.5~7.0	V
DC input voltage	V _{IN}	-0.5~7.0	V
DC output voltage	V _{OUT}	-0.5~V _{CC} + 0.5	V
Input diode current	I _{IK}	-20	mA
Output diode current	lok	±20	mA
DC output current	lout	±25	mA
DC V _{CC} /ground current	Icc	±50	mA
Power dissipation	P _D	180	mW
Storage temperature	T _{stg}	-65~150	°C

Note: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Operating Ranges (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	2.0~5.5	V
Input voltage	V _{IN}	0~5.5	V
Output voltage	V _{OUT}	0~V _{CC}	٧
Operating temperature	T _{opr}	-40~85	°C
Input rise and fall time	dt/dv	0~100 (V _{CC} = 3.3 ± 0.3 V)	ns/V
input rise and rail tillle	ui/uv	0~20 (V _{CC} = 5 ± 0.5 V)	115/V

Note: The operating ranges must be maintained to ensure the normal operation of the device.

Unused inputs must be tied to either VCC or GND.



Electrical Characteristics

DC Characteristics

Characteristics		Symbol Test Condition			Ta = 25°C		Ta = -40~85°C		- Unit			
Characte	HISUCS	Syllibol			V _{CC} (V)	Min	Тур.	Max	Min	Max	Unit	
High level			_		2.0	1.50	_	_	1.50	_	V	
		V _{IH}			3.0~5.5	V _{CC} × 0.7	_	_	V _{CC} × 0.7	_		
Input voltage							_	0.50	_	0.50	V	
	Low level V _{IL} —		3.0~5.5		_	V _{CC} × 0.3	_	V _{CC} × 0.3				
					2.0	1.9	2.0	_	1.9	_	V	
			V _{IN} = V _{IH} or V _{IL}	I _{OH} = -50 μA	3.0	2.9	3.0	_	2.9	_		
Output voltage	High level	V _{OH}			4.5	4.4	4.5	_	4.4			
				$I_{OH} = -4 \text{ mA}$	3.0	2.58	_	_	2.48	_		
				$I_{OH} = -8 \text{ mA}$	4.5	3.94		_	3.80	—		
Output voltage			V _{IN} = V _{IH} or V _{IL}	I _{OL} = 50 μA	2.0	_	0	0.1		0.1		
		w level V _{OL}			3.0	_	0	0.1	_	0.1		
	Low level				4.5	_	0	0.1		0.1		
				$I_{OL} = 4 \text{ mA}$	3.0	_	_	0.36	_	0.44		
				$I_{OL} = 8 \text{ mA}$	4.5	_	_	0.36	_	0.44		
3-state output of	f-state current	loz	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = V_{CC}$ or GND		5.5	_	_	±0.25	_	±2.50	μΑ	
Input leakage cu	rrent	I _{IN}	V _{IN} = 5.5 V or GND		0~5.5	_	_	±0.1	_	±1.0	μА	
Quiescent supply	y current	Icc	$V_{IN} = V_{CC}$ or GND		5.5	_	_	4.0	_	40.0	μΑ	



AC Characteristics (Input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol Test Condition				Ta = 25°C			Ta = -40~85°C		Unit
Characteristics	Symbol	rest Condition	V _{CC} (V)	C _L (pF)	Min	Тур.	Max	Min	Max	Oill
			3.3 ± 0.3	15	_	5.9	8.3	1.0	10.0	
Propagation delay time	t_{pLH}		3.3 ± 0.3	50	_	8.4	11.8	1.0	13.5	- ns
(TC7MH367)	t_{pHL}	_	5.0 ± 0.5	15	_	4.1	5.9	1.0	7.0	
			5.0 ± 0.5	50	_	5.6	7.9	1.0	9.0	
			3.3 ± 0.3	15	_	5.3	7.5	1.0	9.0	
Propagation delay time	t_{pLH}		3.3 ± 0.3	50	_	7.8	11.0	1.0	12.5	ns
(TC7MH368)	t_{pHL}	_	5.0 ± 0.5	15	_	3.8	5.5	1.0	6.5	i iis
			5.0 ± 0.5	50	_	5.3	7.5	1.0	8.5	
	t _{pZL}	$R_L = 1 \text{ k}\Omega$	3.3 ± 0.3	15	_	6.8	10.5	1.0	12.5	- ns
3-state output enable time				50	_	9.3	14.0	1.0	16.0	
3-state output eriable time			5.0 ± 0.5	15	_	4.8	7.2	1.0	8.5	
				50	_	6.3	9.2	1.0	10.5	
3-state output disable time	t _{pLZ}	$R_L = 1 k\Omega$	3.3 ± 0.3	50	_	9.9	13.6	1.0	15.5	ns
5-state output disable time	t _{pHZ}	K[= 1 K22	5.0 ± 0.5	50	_	6.3	9.2	1.0	10.5	115
Output to output skew	t _{osLH}	(NI=t= 4)	3.3 ± 0.3	50	_	_	1.5	_	1.5	ns
Output to output skew	t _{osHL} (Note	(Note 1)	5.0 ± 0.5	50		_	1.0	_	1.0	110
Input capacitance	C _{IN}	_		_	4	10	_	10	pF	
Output capacitance	Cout	_		_	6	_	_	_	pF	
Power dissipation capacitance	C _{PD}			(Note 2)		19	_	_	_	pF

Note 1: Parameter guaranteed by design.

 $t_{\text{OSLH}} = |t_{\text{pLHm}} - t_{\text{pLHn}}|, \, t_{\text{OSHL}} = |t_{\text{pHLm}} - t_{\text{pHLn}}|$

Note 2: CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

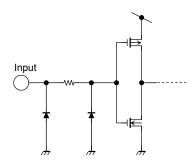
 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/6 (per bit)$



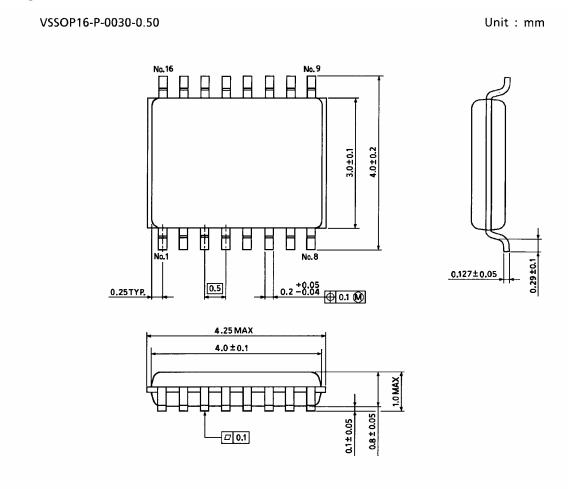
Noise Characteristics (Input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Test Condition		Ta = 25°C		Unit
Characteristics	Symbol	rest condition	V _{CC} (V)	Тур.	Limit	Offic
Quiet output maximum dynamic V _{OL}	VOLP	C _L = 50 pF	5.0	0.4	0.8	V
Quiet output minimum dynamic V _{OL}	V _{OLV}	$C_L = 50 \text{ pF}$	5.0	-0.4	-0.8	٧
Minimum high level dynamic input voltage V_{IH}	V _{IHD}	C _L = 50 pF	5.0	_	3.5	V
Maximum low level dynamic input voltage V_{IL}	V _{ILD}	C _L = 50 pF	5.0	_	1.5	٧

Input Equivalent Circuit



Package Dimensions



Weight: 0.02 g (typ.)

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20070701-EN GENERAL

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